

Amendments to the Claims

The following listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

Claims 1-14 (canceled)

Claim 15 (original): A method for fabricating a capacitor comprising the steps of:

forming a lower electrode on a substrate;

forming a capacitor dielectric film on the lower electrode;

forming an upper electrode on the capacitor dielectric film;

forming an insulation film on the upper electrode;

forming an opening in the insulation film down to the lower electrode;

forming a metal layer on the insulation film; and

substituting a constituent atom of the lower electrode with a metal atom of the metal layer through the opening to thereby form the lower electrode of a metal substituted layer.

Claim 16 (original): A method for fabricating a capacitor comprising the steps of:

forming a lower electrode on a substrate;

forming a capacitor dielectric film on the lower electrode;

forming an upper electrode on the capacitor dielectric film;

forming an insulation film on the upper electrode;

forming in the insulation film a first opening down to the lower electrode and a second opening down to the upper electrode;

forming a metal layer on the insulation film; and

substituting a constituent atom of the lower electrode with a metal atom of the metal layer through the first opening to thereby form the lower electrode of a metal substituted layer and substituting a constituent atom of the upper electrode with a metal atom of the metal layer through the second opening to thereby form the upper electrode of a metal substituted layer.

Claim 17 (original): A method for fabricating a capacitor comprising the steps of:

forming a lower electrode on a substrate;

forming a capacitor dielectric film on the lower electrode;

forming an upper electrode on the capacitor dielectric film;

forming an insulation film on the upper electrode;

forming an opening in the insulation film down to the upper electrode;

forming a metal layer on the insulation film; and

substituting a constituent atom of the upper electrode with a metal atom of the metal layer through the opening to form the upper electrode of a metal substituted layer.

Claim 18 (original): A method for fabricating a capacitor according to claim 15, wherein

a plurality of the sectional electrodes are formed in the step of forming the lower electrode and/or the step of forming the upper electrode.

Claim 19 (original): A method for fabricating a capacitor according to claim 16, wherein
a plurality of the sectional electrodes are formed in the step of forming the lower electrode
and/or the step of forming the upper electrode.

Claim 20 (original): A method for fabricating a capacitor according to claim 17, wherein
a plurality of the sectional electrodes are formed in the step of forming the lower electrode
and/or the step of forming the upper electrode.

Claim 21 (original): A method for fabricating a capacitor according to claim 18, wherein
in the step of forming the lower electrode and/or the step of forming the upper electrode,
the sectional electrodes are formed in a strip-shape;

in the step of forming the opening, a plurality of the openings are formed down to both ends
of the sectional electrodes ; and

in the step of forming the lower electrode of the metal substituted layer and/or the step of
forming the upper electrode of the metal substituted layer, the sectional electrodes are substituted
with the metal from both ends of the sectional electrodes.

Claim 22 (original): A method for fabricating a capacitor according to claim 19, wherein
in the step of forming the lower electrode and/or the step of forming the upper electrode,
the sectional electrodes are formed in a strip-shape;

in the step of forming the opening, a plurality of the openings are formed down to both ends

of the sectional electrodes ; and

in the step of forming the lower electrode of the metal substituted layer and/or the step of forming the upper electrode of the metal substituted layer, the sectional electrodes are substituted with the metal from both ends of the sectional electrodes.

Claim 23 (original): A method for fabricating a capacitor according to claim 20, wherein in the step of forming the lower electrode and/or the step of forming the upper electrode, the sectional electrodes are formed in a strip-shape;

in the step of forming the opening, a plurality of the openings are formed down to both ends of the sectional electrodes; and

in the step of forming the lower electrode of the metal substituted layer and/or the step of forming the upper electrode of the metal substituted layer, the sectional electrodes are substituted with the metal from both ends of the sectional electrodes.

Claim 24 (original): A semiconductor device comprising a capacitor including a lower electrode formed on a substrate, an upper electrode opposed to the lower electrode, and a capacitor dielectric film formed at least between the lower electrode and the upper electrode; and

at least one of the lower electrode and the upper electrode is an electrode of a metal substituted layer.